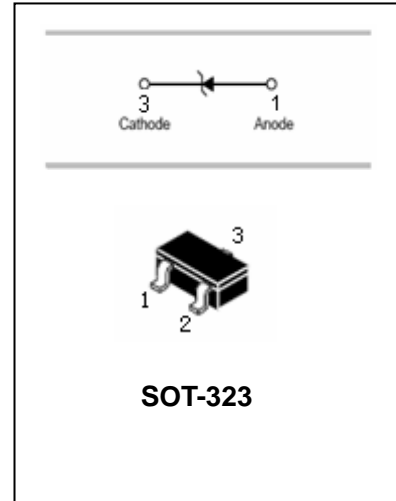


200mW Surface Mount Zener Diode

BZX84C2V4W-BZX84C39W

FEATURES

- Planar Die Construction.
- 200mw Power Dissipation.
- Zener Voltages From 2.4V -51V
- Ideally Suited For Automated Assembly Processes.



APPLICATIONS

- 200Mw Surface mount zener diode

ORDERING INFORMATION

Type No.	Marking	Package Code
BZX84C2V4W-BZX84C39W	See Table on page2	SOT-323

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Forward Voltage@I _F =10mA	V _F	0.9	V
Power Dissipation	P _d	200	mW
Operating and Storage Temperature Range	T _j , T _{stg}	-65 to+150	°C

ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Diode Semiconductor Korea

200mW Surface Mount Zener Diode

BZX84C2V4W-BZX84C39W

Type Number	Marking Code	Zener Voltage Range			Maximum Zener Impedance			Maximum Reverse Current		Typical Temperature Coefficient of Zener Voltage @I _{ZT} mV/°C		
		V _Z @I _{ZT}			I _{ZT}	Z _{ZT} @I _{ZT}	Z _{ZK} @I _{ZK}		I _R	V _R	Min	Max
		Nom(V)	Min(V)	Max(V)	(mA)	(Ω)	(Ω)	(mA)	(μA)	(V)		
BZX84C2V4W	KRB	2.4	2.2	2.6	5.0	100	600	1.0	50	1.0	-3.5	0
BZX84C2V7W	KRC	2.7	2.5	2.9	5.0	100	600	1.0	20	1.0	-3.5	0
BZX84C3V0W	KRD	3.0	2.8	3.2	5.0	95	600	1.0	10	1.0	-3.5	0
BZX84C3V3W	KRE	3.3	3.1	3.5	5.0	95	600	1.0	5.0	1.0	-3.5	0
BZX84C3V6W	KRF	3.6	3.4	3.8	5.0	90	600	1.0	5.0	1.0	-3.5	0
BZX84C3V9W	KRG	3.9	3.7	4.1	5.0	90	600	1.0	3.0	1.0	-3.5	0
BZX84C4V3W	KRH	4.3	4.0	4.6	5.0	90	600	1.0	3.0	1.0	-3.5	0
BZX84C4V7W	KR1	4.7	4.4	5.0	5.0	80	600	1.0	3.0	2.0	-3.5	0.2
BZX84C5V1W	KR2	5.1	4.8	5.4	5.0	60	500	1.0	2.0	2.0	-2.7	1.2
BZX84C5V6W	KR3	5.6	5.2	6.0	5.0	40	480	1.0	1.0	2.0	-2.0	2.5
BZX84C6V2W	KR4	6.2	5.8	6.6	5.0	10	400	1.0	3.0	4.0	0.4	3.7
BZX84C6V8W	KR5	6.8	6.4	7.2	5.0	15	150	1.0	2.0	4.0	1.2	4.5
BZX84C7V5W	KR6	7.5	7.0	7.9	5.0	15	80	1.0	1.0	5.0	2.5	5.3
BZX84C8V2W	KR7	8.2	7.7	8.7	5.0	15	80	1.0	0.7	5.0	3.2	6.2
BZX84C9V1W	KR8	9.1	8.5	9.6	5.0	15	80	1.0	0.5	6.0	3.8	7.0
BZX84C10W	KR9	10	9.4	10.6	5.0	20	100	1.0	0.2	7.0	4.5	8.0
BZX84C11W	KP1	11	10.4	11.6	5.0	20	150	1.0	0.1	8.0	5.4	9.0
BZX84C12W	KP2	12	11.4	12.7	5.0	25	150	1.0	0.1	8.0	6.0	10.0
BZX84C13W	KP3	13	12.4	14.1	5.0	30	150	1.0	0.1	8.0	7.0	11.0
BZX84C15W	KP4	15	13.8	15.6	5.0	30	170	1.0	0.1	10.5	9.2	13.0
BZX84C16W	KP5	16	15.3	17.1	5.0	40	200	1.0	0.1	11.2	10.4	14.0
BZX84C18W	KP6	18	16.8	19.1	5.0	45	200	1.0	0.1	12.6	12.4	16.0
BZX84C20W	KP7	20	18.8	21.2	5.0	55	225	1.0	0.1	14.0	14.4	18.0
BZX84C22W	KP8	22	20.8	23.3	5.0	55	225	1.0	0.1	15.4	16.4	20.0
BZX84C24W	KP9	24	22.8	25.6	5.0	70	250	1.0	0.1	16.8	18.4	22.0

Diode Semiconductor Korea

200mW Surface Mount Zener Diode

BZX84C2V4W-BZX84C39W

Type Number	Marking Code	Zener Voltage Range			Maximum Zener Impedance			Maximum Reverse Current		Typical Temperature Coefficient of Zener Voltage @ I_{ZT} mV/°C		
		$V_Z@I_{ZT}$			I_{ZT}	$Z_{ZT}@I_{ZT}$	$Z_{ZK}@I_{ZK}$		I_R	V_R	Min	Max
		Nom(V)	Min(V)	Max(V)	(mA)	(Ω)	(Ω)	(mA)	(μ A)	(V)		
BZX84C27W	KPA	27	25.1	28.9	2.0	80	250	0.5	0.1	18.9	21.4	25.3
BZX84C30W	KPB	30	28.0	32.0	2.0	80	300	0.5	0.1	21.0	24.4	29.4
BZX84C33W	KPC	33	31.0	35.0	2.0	80	300	0.5	0.1	23.1	27.4	33.4
BZX84C36W	KPD	36	34.0	38.0	2.0	90	325	0.5	0.1	25.2	30.4	37.4
BZX84C39W	KPE	39	37.0	41.0	2.0	130	350	0.5	0.1	27.3	33.4	41.2

TYPICAL CHARACTERISTICS @ $T_a=25^\circ\text{C}$ unless otherwise specified

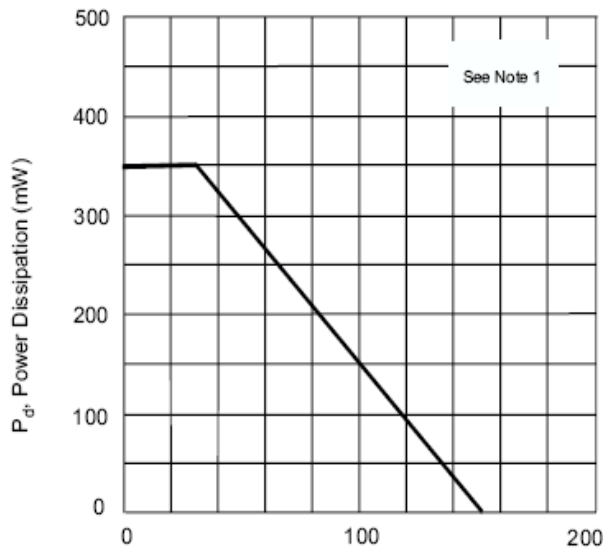


Fig. 1 Power Derating Curve

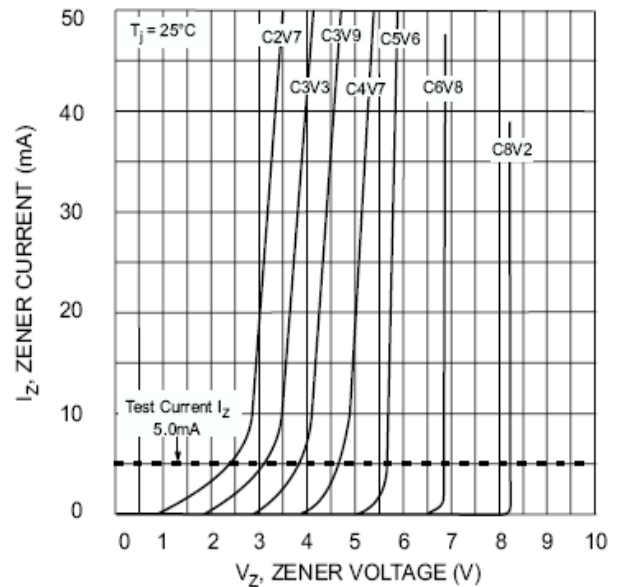


Fig. 2 Zener Breakdown Characteristics

200mW Surface Mount Zener Diode

BZX84C2V4W-BZX84C39W

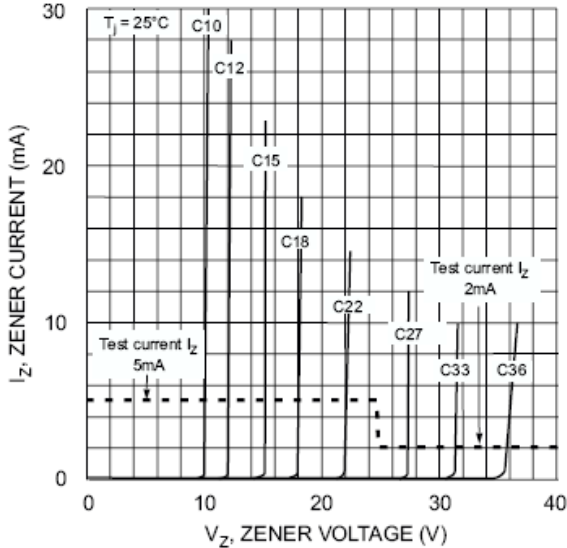


Fig. 3 Zener Breakdown Characteristics

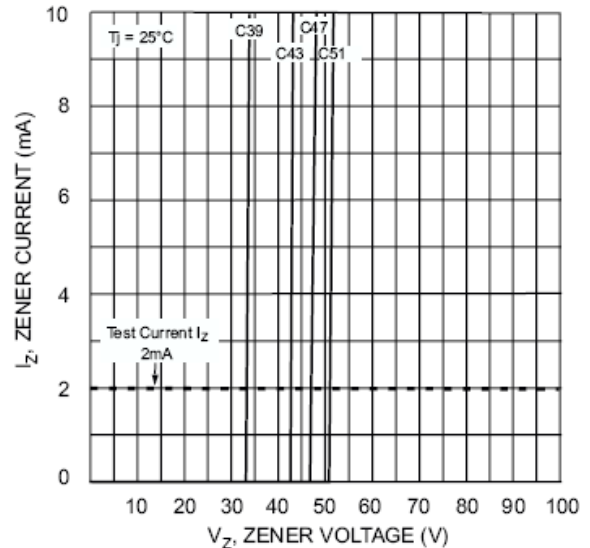


Fig. 4 Zener Breakdown Characteristics

PACKAGE OUTLINE

Plastic surface mounted package

SOT-23

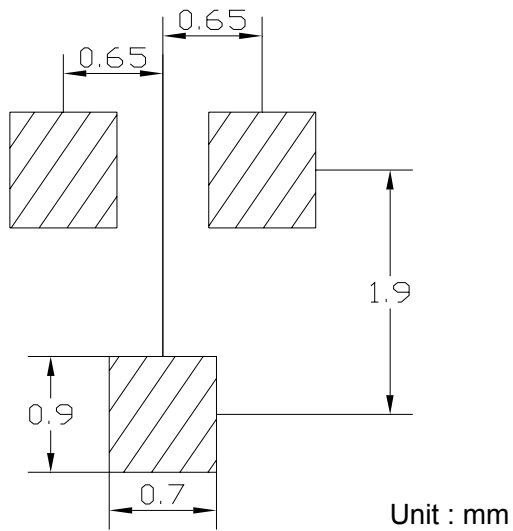
SOT-323		
Dim	Min	Max
A	1.8	2.2
B	1.15	1.35
C	1.0Typical	
D	0.15	0.35
E	0.25	0.40
G	1.2	1.4
H	0.02	0.1
J	0.1Typical	
K	2.1	2.3
All Dimensions in mm		

Diode Semiconductor Korea

200mW Surface Mount Zener Diode

BZX84C2V4W-BZX84C39W

SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
BZX84C2V4W-BZX84C39W	SOT-323	3000/Tape&Reel